STL23NM50N

N-channel 500 V, 0.170 Ω typ., 14 A MDmesh™ II Power MOSFET in a PowerFLAT™ 8x8 HV package

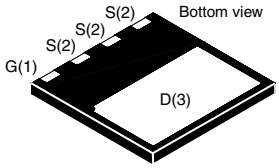
Datasheet — production data

Features

Type	V_{DSS} @ T_{Jmax}	$R_{DS(on)}$ max	I_D
STL23NM50N	550 V	< 0.210 Ω	14 A (1)

1. The value is rated according to $R_{thj\text{-}case}$

- 100% avalanche tested
- Low input capacitance and gate charge
- Low gate input resistance



PowerFLAT™ 8x8 HV

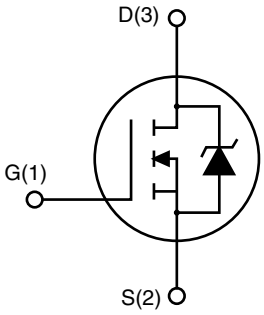
Applications

- Switching applications

Description

This device is an N-channel Power MOSFET developed using the second generation of MDmesh™ technology. This revolutionary Power MOSFET associates a vertical structure to the company's strip layout to yield one of the world's lowest on-resistance and gate charge. It is therefore suitable for the most demanding high efficiency converters.

Figure 1. Internal schematic diagram



AM01475v1

Table 1. Device summary

Order code	Marking	Package	Packaging
STL23NM50N	23NM50N	PowerFLAT™ 8x8 HV	Tape and reel

This is information on a product in full production. www.st.com

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1 Electrical ratings

Table 2. Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{DS}	Drain-source voltage (V_{GS} = 0)	500	V
V_{GS}	Gate-source voltage	± 25	V
I_D (1)	Drain current (continuous) at T_C = 25 °C	14	A
I_D (1)	Drain current (continuous) at T_C = 100 °C	11	A
I_D(3)	Drain current (continuous) at T_{amb} = 25 °C	2.8	A
I_D(3)	Drain current (continuous) at T_{amb} = 100 °C	2.1	A
I_{DM} (1),(2)	Drain current (pulsed)	56	A
P_{TOT} (3)	Total dissipation at T_{amb} = 25 °C	3	W
P_{TOT}(1)	Total dissipation at T_C = 25 °C	125	W
I_{AR}	Avalanche current, repetitive or not-repetitive (pulse width limited by T_j max)	4	A
E_{AS}	Single pulse avalanche energy (starting T_j = 25 °C, I_D = I_{AR}, V_{DD} = 50 V)	300	mJ
dv/dt (4)	Peak diode recovery voltage slope	15	V/ns
T_{stg}	Storage temperature	- 55 to 150	°C
T_j	Max. operating junction temperature	150	°C

1. The value is rated according to $R_{thj\text{-}case}$
2. Pulse width limited by safe operating area
3. When mounted on FR-4 board of inch², 2oz Cu
4. I_{SD} ≤ 14 A, di/dt ≤ 400 A/µs, $V_{DSpeak} \leq V_{(BR)DSS}$, V_{DD} = 80% $V_{(BR)DSS}$

Table 3. Thermal data

Symbol	Parameter	Value	Unit
$R_{thj\text{-}case}$	Thermal resistance junction-case max	1	°C/W
$R_{thj\text{-}amb}$(1)	Thermal resistance junction-amb max	45	°C/W

1. When mounted on 1inch² FR-4 board, 2 oz Cu

2 Electrical characteristics

(T_C = 25 °C unless otherwise specified)

Table 4. On /off states

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	I_D = 1 mA, V_{GS} = 0	500			V
I_{DSS}	Zero gate voltage drain current V_{DS} = Max rating V_{DS} = Max rating, T_C=125 °C V_{GS} = 0				1 100	µA µA
I_{GSS}	Gate-body leakage current	V_{GS} = ± 25 V, V_{DS} = 0			100	nA
$V_{GS(th)}$	Gate threshold voltage	V_{DS} = V_{GS}, I_D = 250 µA	2	3	4	V
$R_{DS(on)}$	Static drain-source on-resistance	V_{GS} = 10 V, I_D = 7 A		0.170	0.210	Ω

Table 5. Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss} C_{oss} C_{rss}	Input capacitance Output capacitance Reverse transfer capacitance	V_{DS} = 50 V, f = 1 MHz, V_{GS} = 0	-	1330 84 4.8	-	pF pF pF
$C_{oss\ eq.}$ (1)	Equivalent output capacitance	V_{GS} = 0, V_{DS} = 0 to 400 V	-	210	-	pF
Q_g Q_{gs} Q_{gd}	Total gate charge Gate-source charge Gate-drain charge	V_{DD} = 400 V, I_D = 17 A, V_{GS} = 10 V, *(see Figure 14)*	-	45 7 24	-	nC nC nC
R_g	Gate input resistance	f=1 MHz Gate DC Bias=0 Test signal level=20 mV open drain	-	4.6	-	Ω

1. $C_{oss\ eq.}$ is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DS}

Table 6. Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$ t_r $t_{d(off)}$ t_f	Turn-on delay time Rise time Turn-off-delay time Fall time	V_{DD} = 250 V, I_D = 17 A R_G = 4.7 Ω V_{GS} = 10 V *(see Figure 13)*	-	6.6 19 71 29	-	ns ns ns ns

Table 7. Source drain diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
I_{SD} I_{SDM} (1)	Source-drain current Source-drain current (pulsed)		-		17 68	A A
V_{SD} (2)	Forward on voltage	I_{SD} = 17 A, V_{GS} = 0	-		1.5	V
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 17 A, di/dt = 100 A/µs V_{DD} = 60 V *(see Figure 18)*	-	286 3700 26		ns nC A
t_{rr} Q_{rr} I_{RRM}	Reverse recovery time Reverse recovery charge Reverse recovery current	I_{SD} = 17 A, di/dt = 100 A/µs V_{DD} = 60 V, T_j = 150 °C *(see Figure 18)*	-	350 4800 27		ns nC A

1. Pulse width limited by safe operating area
2. Pulsed: pulse duration = 300 µs, duty cycle 1.5%

2.1 Electrical characteristics (curves)

Figure 2. Safe operating area

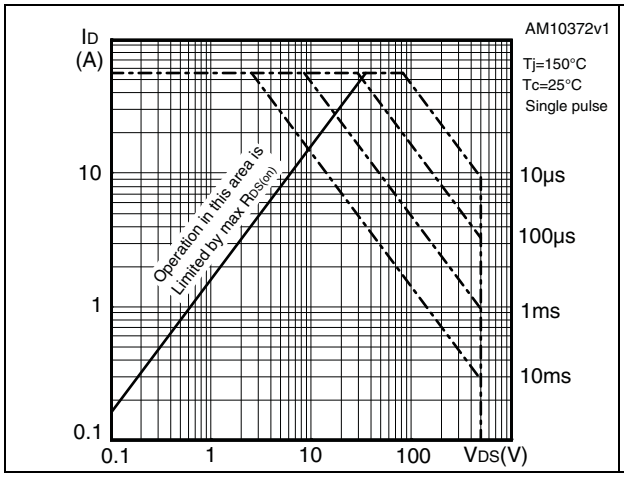


Figure 3. Thermal impedance

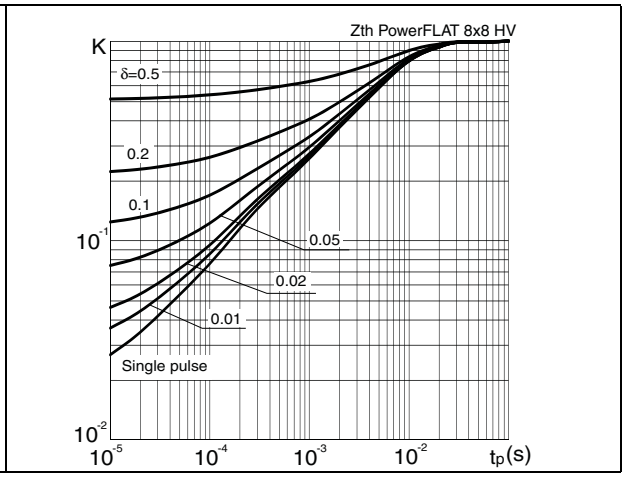


Figure 4. Output characteristics

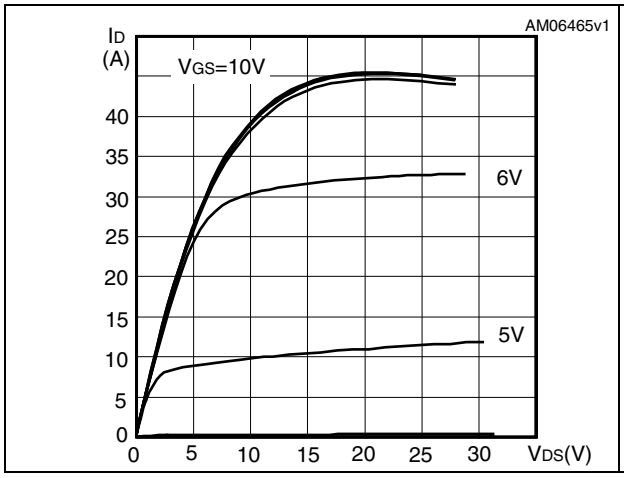


Figure 5. Transfer characteristics

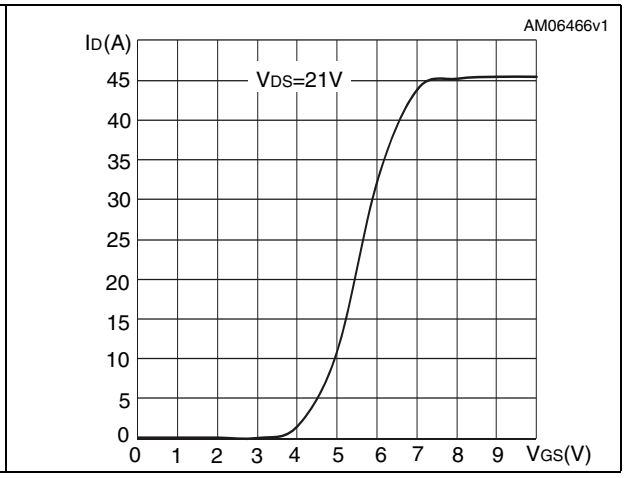


Figure 6. Normalized B_{VDSS} vs temperature

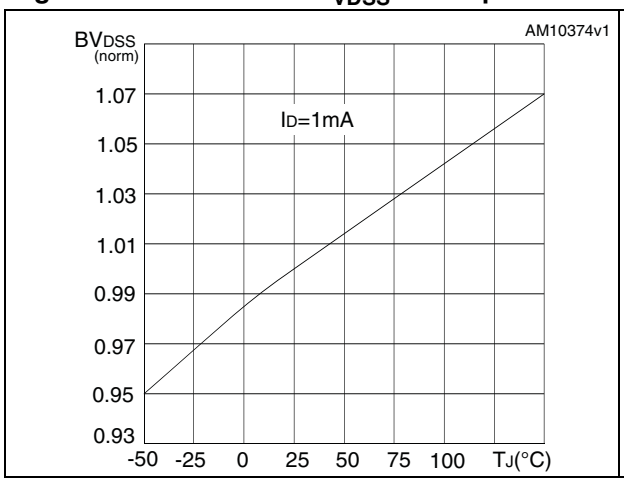


Figure 7. Static drain-source on-resistance

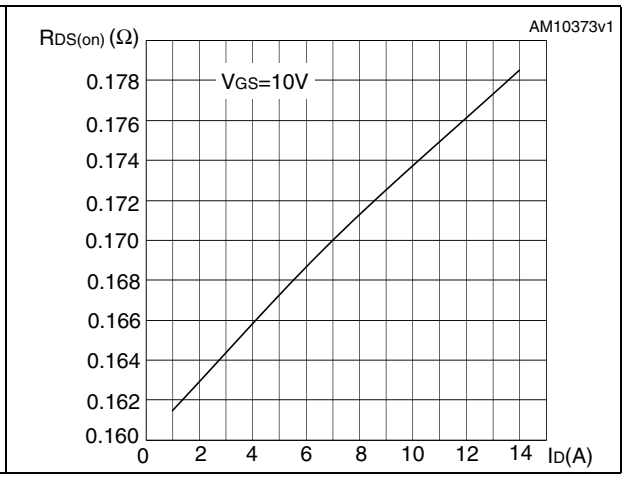


Figure 8. Gate charge vs gate-source voltage

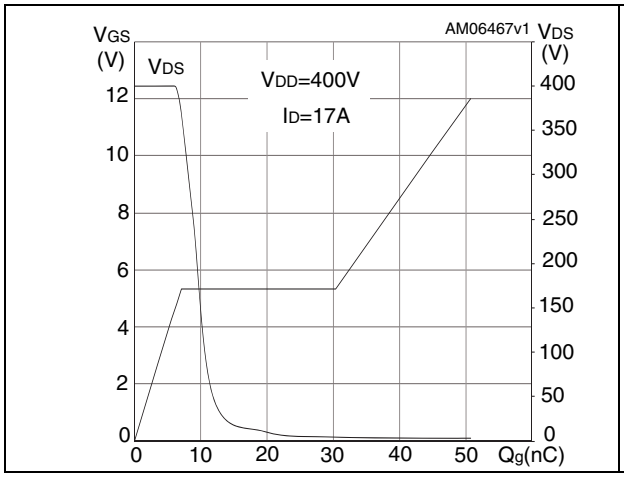


Figure 9. Capacitance variations

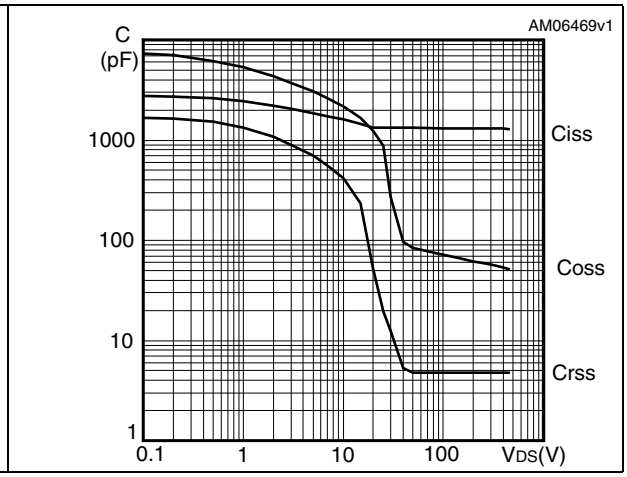


Figure 10. Normalized gate threshold voltage vs temperature

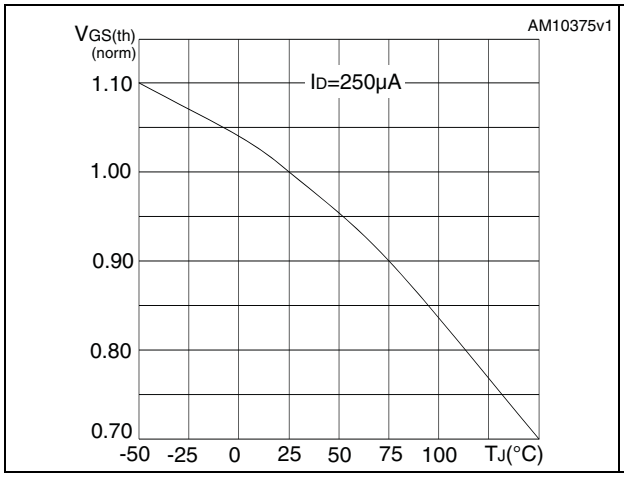


Figure 11. Normalized on-resistance vs temperature

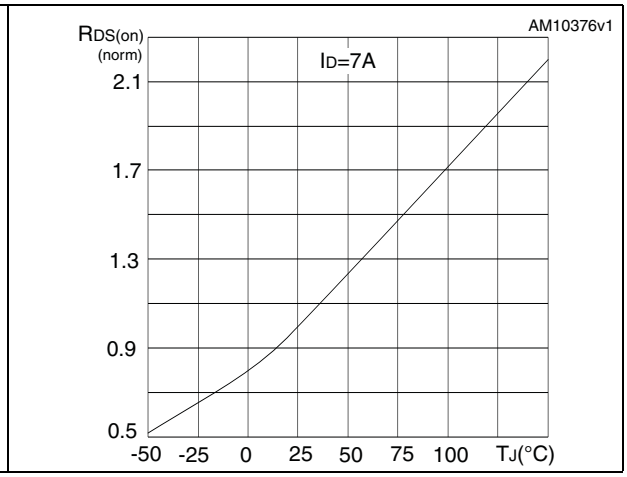
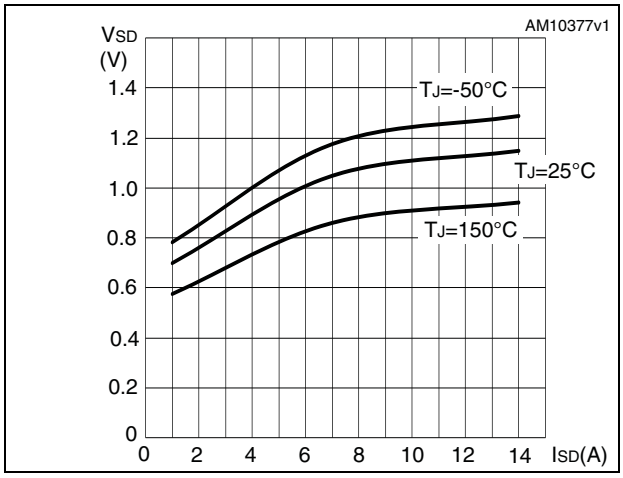


Figure 12. Source-drain diode forward characteristics



3 Test circuits

Figure 13. Switching times test circuit for resistive load

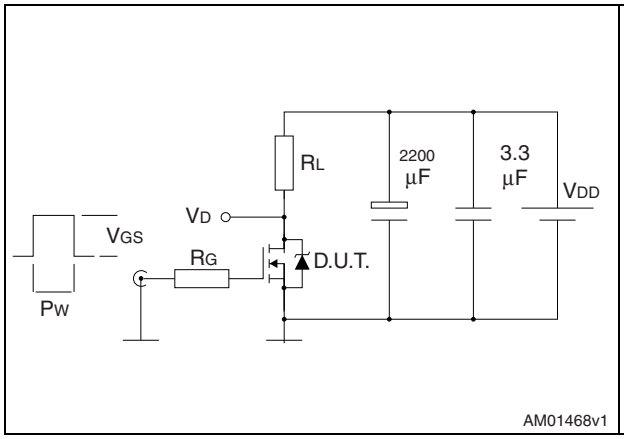


Figure 14. Gate charge test circuit

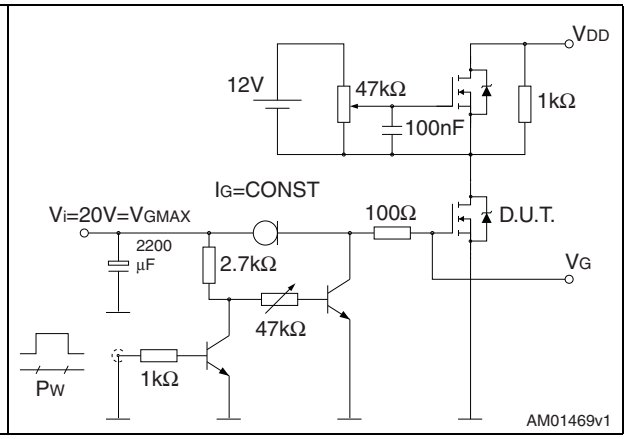


Figure 15. Test circuit for inductive load switching and diode recovery times

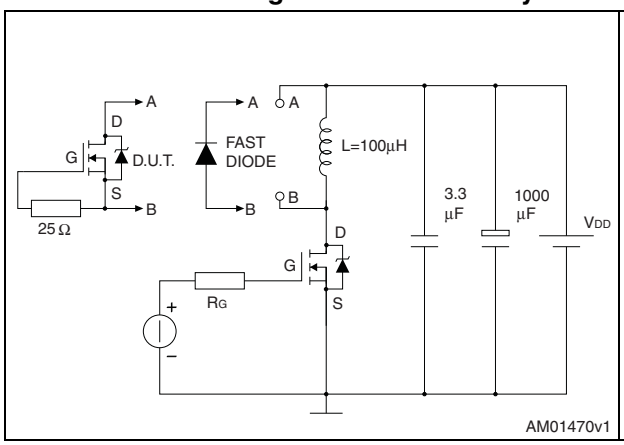


Figure 16. Unclamped inductive load test circuit

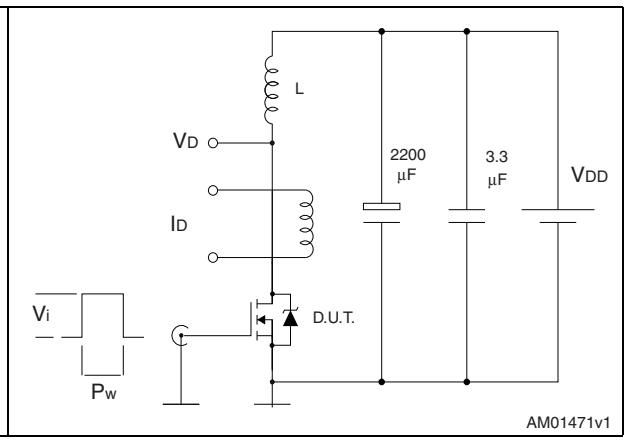


Figure 17. Unclamped inductive waveform

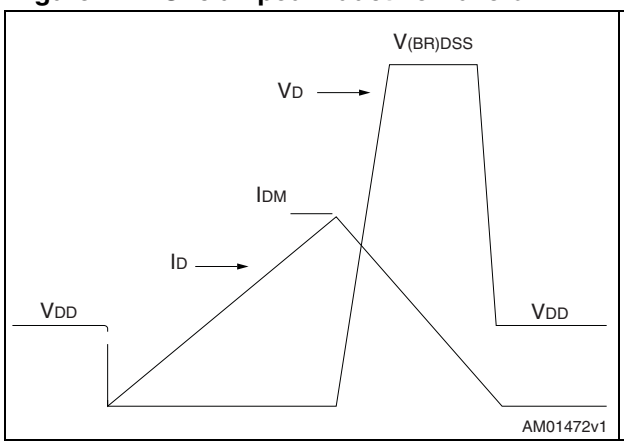
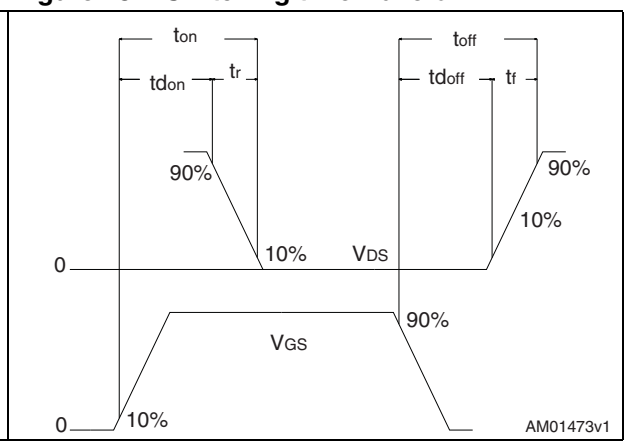


Figure 18. Switching time waveform



4 Package mechanical data

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK® packages, depending on their level of environmental compliance. ECOPACK® specifications, grade definitions and product status are available at: www.st.com. ECOPACK is an ST trademark.

Table 8. PowerFLAT™8x8 HV mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80	0.90	1.00
A1	0.00	0.02	0.05
b	0.95	1.00	1.05
D		8.00	
E		8.00	
D2	7.05	7.20	7.30
E2	4.15	4.30	4.40
e		2.00	
L	0.40	0.50	0.60
aaa		0.10	
bbb		0.10	
ccc		0.10	

Figure 19. PowerFLAT™ 8x8 HV drawing mechanical data

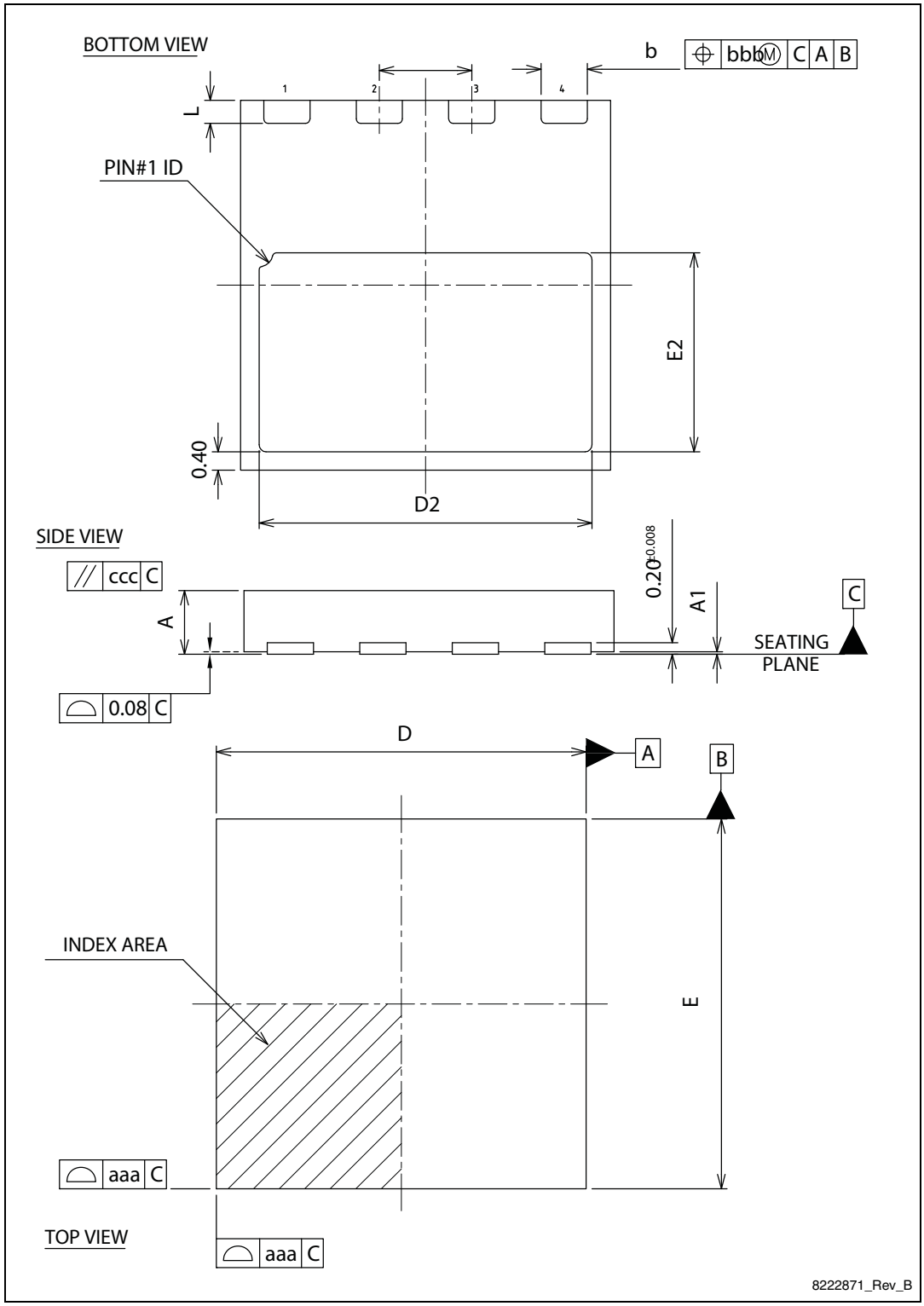
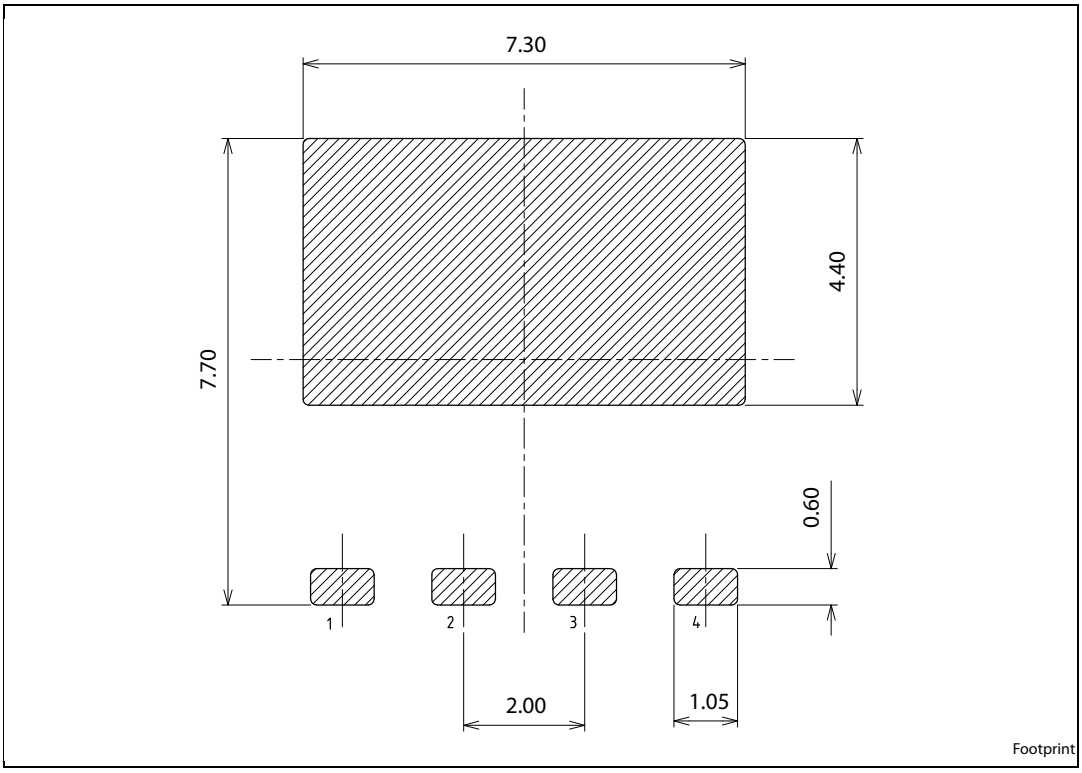


Figure 20. PowerFLAT™ 8x8 HV recommended footprint



5 Revision history

Table 9. Document revision history

Date	Revision	Changes
10-Oct-2011	1	First release.
08-Oct-2012	2	Updated title on the cover page. Updated value for dv/dt on *Table 2: Absolute maximum ratings*. Document status promoted from preliminary to production data.

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